< Dual-In-Line Package Intelligent Power Module >

**PSS15S92F6-AG**
**PSS15S92E6-AG**

TRANSFER MOLDING TYPE
INSULATED TYPE

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### OUTLINE

### MAIN FUNCTION AND RATINGS

- 3 phase DC/AC inverter
- 600V / 15A (CSTBT)
- N-side IGBT open emitter
- Built-in bootstrap diodes with current limiting resistor

### APPLICATION

- AC 100~240Vrms (DC voltage: 400V or below) class
  low power motor control

### TYPE NAME

<table>
<thead>
<tr>
<th>Type</th>
<th>Function</th>
</tr>
</thead>
<tbody>
<tr>
<td>PSS15S92F6-AG</td>
<td>With temperature output function</td>
</tr>
<tr>
<td>PSS15S92E6-AG</td>
<td>With OT protection function</td>
</tr>
</tbody>
</table>

### INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS

- **For P-side**
  - Drive circuit, High voltage high-speed level shifting, Control supply under-voltage (UV) protection
- **For N-side**
  - Drive circuit, Control supply under-voltage protection (UV), Short circuit protection (SC), Over temperature protection (OT, PSS15S92E6-AG only)
- Fault signaling: Corresponding to SC fault (N-side IGBT), UV fault (N-side supply) and OT fault
- Temperature output: Outputting LVIC temperature by analog signal (PSS15S92F6-AG only)
- Input interface: 3.5V line, Schmitt trigger receiver circuit (High Active)
- UL Recognized: UL1557 File E323585

### INTERNAL CIRCUIT

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Vot(16)
Vot(17)

---

CIN(15)

---

Fot(14)

---

Vot(10)
Vot(11)
Vot(12)
Vot(13)

---

Vot(5)
Vot(6)
Vot(7)
Vot(8)

---

Uo(5)

---

Uo(10)

---

NU(20)

---

NV(19)

---

NW(18)

---

VNC(9)

---

UN(10)

---

VN(11)

---

WN(12)

---

P(24)

---

U(23)

---

V(22)

---

W(21)

---

NW(21)

---

CIN(15)

---

HVIC

---

IGBT1

---

Di1

---

IGBT2

---

Di2

---

IGBT3

---

Di3

---

IGBT4

---

Di4

---

IGBT5

---

Di5

---

IGBT6

---

Di6

---

Built-in temperature output type: Vot
(PSS**S92E6-AG)

Built-in OT type: NC (No Connection)
(PSS**S92F6-AG)
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MAXIMUM RATINGS (Tj = 25°C, unless otherwise noted)

### INVERTER PART

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Condition</th>
<th>Ratings</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>VCC</td>
<td>Supply voltage</td>
<td>Applied between P-NU, NV, NW</td>
<td>450</td>
<td>V</td>
</tr>
<tr>
<td>VCC(surge)</td>
<td>Supply voltage (surge)</td>
<td>Applied between P-NU, NV, NW</td>
<td>500</td>
<td>V</td>
</tr>
<tr>
<td>VCEG</td>
<td>Collector-emitter voltage</td>
<td></td>
<td>600</td>
<td>V</td>
</tr>
<tr>
<td>±IC</td>
<td>Each IGBT collector current</td>
<td>Tj= 25°C, less than 1ms</td>
<td>15</td>
<td>A</td>
</tr>
<tr>
<td>±ICP</td>
<td>Each IGBT collector current (peak)</td>
<td>Tj= 25°C, less than 1ms</td>
<td>30</td>
<td>A</td>
</tr>
<tr>
<td>PCE</td>
<td>Collector dissipation</td>
<td>Tj= 25°C, per 1 chip</td>
<td>27.0</td>
<td>W</td>
</tr>
<tr>
<td>TJ</td>
<td>Junction temperature</td>
<td>(Note 1)</td>
<td>-30~+150</td>
<td>°C</td>
</tr>
</tbody>
</table>

Note 1: The maximum junction temperature rating of built-in power chips is 150°C(@Tcs≤100°C). However, to ensure safe operation of DIPIPM, the average junction temperature should be limited to Tj(Ave)≤125°C (@Tcs≤100°C).

### CONTROL (PROTECTION) PART

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Condition</th>
<th>Ratings</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>V0</td>
<td>Control supply voltage</td>
<td>Applied between VP1-VNC, VN1-VNC</td>
<td>20</td>
<td>V</td>
</tr>
<tr>
<td>V0B</td>
<td>Control supply voltage</td>
<td>Applied between VUFB-U, VVFB-V, VWFB-W</td>
<td>20</td>
<td>V</td>
</tr>
<tr>
<td>VIN</td>
<td>Input voltage</td>
<td>Applied between UN, VN, WN</td>
<td>-0.5~V0+0.5</td>
<td>V</td>
</tr>
<tr>
<td>VFO</td>
<td>Fault output supply voltage</td>
<td>Applied between FC-VNC</td>
<td>-0.5~V0+0.5</td>
<td>V</td>
</tr>
<tr>
<td>IF0</td>
<td>Fault output current</td>
<td>Sink current at F0 terminal</td>
<td>1</td>
<td>mA</td>
</tr>
<tr>
<td>VSCI</td>
<td>Current sensing input voltage</td>
<td>Applied between CIN-VNC</td>
<td>-0.5~V0+0.5</td>
<td>V</td>
</tr>
</tbody>
</table>

### TOTAL SYSTEM

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Condition</th>
<th>Ratings</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>VCC(PROT)</td>
<td>Self protection supply voltage (Short circuit protection capability)</td>
<td>V0 = 13.5~16.5V, Inverter Part</td>
<td>400</td>
<td>V</td>
</tr>
<tr>
<td>Tc</td>
<td>Module case operation temperature</td>
<td>Measurement point of Tc is provided in Fig.1</td>
<td>-30~+100</td>
<td>°C</td>
</tr>
<tr>
<td>Tsc</td>
<td>Storage temperature</td>
<td></td>
<td>-40~+125</td>
<td>°C</td>
</tr>
<tr>
<td>VISO</td>
<td>Isolation voltage</td>
<td>60Hz, Sinusoidal, AC 1min, between connected all pins and heat sink plate</td>
<td>1500</td>
<td>Vrms</td>
</tr>
</tbody>
</table>

Fig. 1: TC MEASUREMENT POINT

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Condition</th>
<th>Limits</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>Rth(j-c)Q</td>
<td>Junction to case thermal resistance (per 1/6 module)</td>
<td>Inverter IGBT part</td>
<td>3.7</td>
<td>kW</td>
</tr>
<tr>
<td>Rth(j-c)F</td>
<td>Junction to case thermal resistance (per 1/6 module)</td>
<td>Inverter FWDI part</td>
<td>4.5</td>
<td>kW</td>
</tr>
</tbody>
</table>

Note 2: Grease with good thermal conductivity and long-term endurance should be applied evenly with about +100μm~+200μm on the contacting surface of DIPIPM and heat sink. The contacting thermal resistance between DIPIPM case and heat sink Rth(c-f) is determined by the thickness and the thermal conductivity of the applied grease. For reference, Rth(c-f) is about 0.3K/W (per 1/6 module, grease thickness: 20μm, thermal conductivity: 1.0W/m•K).
TRANSFER MOLDING TYPE

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INVERTER PART

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter Description</th>
<th>Condition</th>
<th>Limits</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>$V_{CE(sat)}$</td>
<td>Collector-emitter saturation voltage</td>
<td>$V_{CE}=V_{BE}=15V, V_{IH}=5V$</td>
<td>$I_C=15A, T_J=25°C$</td>
<td>-</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>$I_C=15A, T_J=125°C$</td>
<td>-</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>$I_C=1.5A, T_J=25°C$</td>
<td>-</td>
</tr>
<tr>
<td>$V_{CE}$</td>
<td>FWDi forward voltage</td>
<td>$V_{CE}=0V, I_C=15A$</td>
<td>-</td>
<td>2.50</td>
</tr>
<tr>
<td>$t_{on}$</td>
<td>Switching times</td>
<td>$V_{CE}=300V, V_{CE}=15V$</td>
<td>-</td>
<td>0.65</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>$I_C=15A, T_J=125°C, V_{CE}=0→5V$</td>
<td>-</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>Inductive Load (upper-lower arm)</td>
<td>-</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td>-</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>$I_{CES}$</td>
<td>Collector-emitter cut-off current</td>
<td>$V_{CE}=V_{CES}$</td>
<td>$T_J=25°C$</td>
<td>-</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>$T_J=125°C$</td>
<td>-</td>
</tr>
</tbody>
</table>

CONTROL (PROTECTION) PART

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter Description</th>
<th>Condition</th>
<th>Limits</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>$I_D$</td>
<td>Circuit current</td>
<td>Total of $V_{IN}, V_{NC}, IN, V_{NC}$</td>
<td>$V_{CC}=15V, V_{IN}=0V$</td>
<td>-</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>$V_{CC}=15V, V_{IN}=5V$</td>
<td>-</td>
</tr>
<tr>
<td></td>
<td></td>
<td>Each part of $V_{IN}=U, V_{IN}=V, V_{IN}=W, V_{IN}=V_U, V_{IN}=V_D$</td>
<td>$V_{CC}=V_{CC}=15V, V_{IN}=0V$</td>
<td>-</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>$V_{CC}=V_{CC}=15V, V_{IN}=5V$</td>
<td>-</td>
</tr>
<tr>
<td>$V_{SC(th)}$</td>
<td>Short circuit trip level</td>
<td>$V_{SC}=15V$</td>
<td>(Note 3)</td>
<td>0.455</td>
</tr>
<tr>
<td>$V_{UV}$</td>
<td>P-side Control supply</td>
<td>Under-voltage protection(UV)</td>
<td>$T_J≤125°C$</td>
<td>Trip level</td>
</tr>
<tr>
<td>$V_{UV}$</td>
<td>N-side Control supply</td>
<td>Under-voltage protection(UV)</td>
<td>Trip level</td>
<td>7.0</td>
</tr>
<tr>
<td>$V_{OT}$</td>
<td>Temperature Output (PSS**S92E6-AG)</td>
<td>Pull down R=5kΩ (Note 4)</td>
<td>LVIC Temperature=90°C</td>
<td>2.63</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>LVIC Temperature=25°C</td>
<td>0.88</td>
</tr>
<tr>
<td>$V_{OT}$</td>
<td>Over temperature protection (OT, PSS**S92E6-AG) (Note 5)</td>
<td>$V_{OT}=15V$</td>
<td>Trip level</td>
<td>100</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>Detect LVIC temperature</td>
<td>-</td>
</tr>
<tr>
<td>$V_{FNC}$</td>
<td>Fault output voltage</td>
<td>$V_{FNC}=0V, F_{DNC}$ terminal pulled up to 5V by 10kΩ</td>
<td>4.9</td>
<td>-</td>
</tr>
<tr>
<td>$V_{FOL}$</td>
<td>Fault output pulse width</td>
<td>$V_{FNC}=1V, I_{FOL}=1mA$</td>
<td>-</td>
<td>-</td>
</tr>
<tr>
<td>$I_{FNC}$</td>
<td>Input current</td>
<td>$V_{IN}=5V$</td>
<td>0.70</td>
<td>1.00</td>
</tr>
<tr>
<td>$V_{BKH}$</td>
<td>ON threshold voltage</td>
<td></td>
<td>-</td>
<td>2.10</td>
</tr>
<tr>
<td>$V_{BKH}$</td>
<td>OFF threshold voltage</td>
<td></td>
<td></td>
<td>0.80</td>
</tr>
<tr>
<td>$V_{BKHP}$</td>
<td>ON/OFF threshold hysteresis voltage</td>
<td></td>
<td></td>
<td>0.35</td>
</tr>
<tr>
<td>$V_{F}$</td>
<td>Bootstrap Di forward voltage</td>
<td>$I_{D}=10mA$ including voltage drop by limiting resistor</td>
<td>(Note 7)</td>
<td>1.1</td>
</tr>
<tr>
<td>$R$</td>
<td>Built-in limiting resistance</td>
<td>Included in bootstrap Di</td>
<td>80</td>
<td>100</td>
</tr>
</tbody>
</table>

Note 3: SC protection works only for N-side IGBT. Please select the external shunt resistance such that the SC trip-level is less than 1.7 times the current rating.

4: DIPPM don't shutdown IGBTs and output fault signal automatically when the temperature exceeds excessively. When temperature exceeds the protective level that user defined, controller (MCU) should stop the DIPPM. Temperature of LVCIC vs. $V_{OT}$ output characteristics is described in Fig. 3.

5: When the LVIC temperature exceeds OT trip temperature level($OT_t$), OT protection works and Fo outputs. In that case if the heat sink dropped off or fixed loosely, don’t reuse that DIPPM. (There is a possibility that junction temperature of power chips exceeded maximum $T_j(150°C)$.)

6: Fault signal Fo outputs when SC, UV or OT protection works. Fo pulse width is different for each protection modes. At SC failure, Fo pulse width is a fixed width (minimum 20μs), but at UV or OT failure, Fo outputs continuously until recovering from UV or OT state. (But minimum Fo pulse width is 20μs.)

7: The characteristics of bootstrap Di is described in Fig. 2.

Fig. 2 Characteristics of bootstrap Di $V_{F}-I_{F}$ curve (@$T_a=25°C$) including voltage drop by limiting resistor (Right chart is enlarged chart.)
Fig. 3 Temperature of LVIC vs. V\textsubscript{OT} output characteristics

![Diagram of temperature vs. V\textsubscript{OT} output characteristics]

**Fig. 4 V\textsubscript{OT} output circuit**

1. It is recommended to insert 5kΩ (5.1kΩ is recommended) pull down resistor for getting linear output characteristics at low temperature below room temperature. When the pull down resistor is inserted between V\textsubscript{OT} and V\textsubscript{NC} (control GND), the extra circuit current, which is calculated approximately by V\textsubscript{OT} output voltage divided by pull down resistance, flows as LVIC circuit current continuously. In the case of using V\textsubscript{OT} for detecting high temperature over room temperature only, it is unnecessary to insert the pull down resistor.

2. In the case of using V\textsubscript{OT} with low voltage controller like 3.3V MCU, V\textsubscript{OT} output might exceed control supply voltage 3.3V when temperature rises excessively. If system uses low voltage controller, it is recommended to insert a clamp D1 between control supply of the controller and V\textsubscript{OT} output for preventing over voltage destruction.

3. In the case of not using V\textsubscript{OT}, leave V\textsubscript{OT} output NC (No Connection).

Refer the application note for Super Mini DIPiPM Ver.5 series about the usage of V\textsubscript{OT}.
MECHANICAL CHARACTERISTICS AND RATINGS

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Condition</th>
<th>Limits</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>Mounting torque</td>
<td>Mounting screw: M3 (Note 8)</td>
<td>Recommended</td>
<td>0.69N·m</td>
</tr>
<tr>
<td>Terminal pulling strength</td>
<td>Control terminal: Load 4.9N</td>
<td>EIAJ-ED-4701</td>
<td>10</td>
</tr>
<tr>
<td>Terminal bending strength</td>
<td>Control terminal: Load 2.45N</td>
<td>EIAJ-ED-4701</td>
<td>2</td>
</tr>
<tr>
<td>Weight</td>
<td></td>
<td></td>
<td>-</td>
</tr>
<tr>
<td>Heat-sink flatness</td>
<td>(Note 9)</td>
<td>-50</td>
<td>100</td>
</tr>
</tbody>
</table>

Note 8: Plain washers (ISO 7089~7094) are recommended.
Note 9: Measurement point of heat sink flatness

RECOMMENDED OPERATION CONDITIONS

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Condition</th>
<th>Limits</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>V_CC</td>
<td>Supply voltage</td>
<td>Applied between P-N, N, N</td>
<td>0</td>
<td>400</td>
</tr>
<tr>
<td>V_D</td>
<td>Control supply voltage</td>
<td>Applied between V_FB-VNC, V_NC-VNC, V_DC-VNC</td>
<td>13.5</td>
<td>16.5</td>
</tr>
<tr>
<td>V_FB</td>
<td>Control supply voltage</td>
<td>Applied between V_FB-U, V_FB-V, V_FB-W</td>
<td>13.0</td>
<td>18.5</td>
</tr>
<tr>
<td>ΔV_D, ΔV_FB</td>
<td>Control supply variation</td>
<td></td>
<td>-1</td>
<td>+1</td>
</tr>
<tr>
<td>I_PWM</td>
<td>PWM input frequency</td>
<td>T_C ≤ 100°C, T_J ≤ 125°C</td>
<td>-3</td>
<td>20</td>
</tr>
<tr>
<td>I_O</td>
<td>Allowable r.m.s. current</td>
<td>V_CC = 300V, V_D = 15V, P.F = 0.8, Sinusoidal PWM</td>
<td>f_PWM= 5kHz</td>
<td>-</td>
</tr>
<tr>
<td>PWIN(on)</td>
<td>Minimum input pulse width</td>
<td></td>
<td>0.7</td>
<td>-</td>
</tr>
<tr>
<td>PWIN(off)</td>
<td></td>
<td>(Note 11)</td>
<td>0.7</td>
<td>-</td>
</tr>
<tr>
<td>V_NC</td>
<td>V_NC variation</td>
<td>Between V_NC-N, N, N (including surge)</td>
<td>-5</td>
<td>+5</td>
</tr>
<tr>
<td>T_J</td>
<td>Junction temperature</td>
<td></td>
<td>-20</td>
<td>+125</td>
</tr>
</tbody>
</table>

Note 10: Allowable r.m.s. current depends on the actual application conditions.
Note 11: DIIPIM might not make response if the input signal pulse width is less than PWIN(on), PWIN(off).
Fig. 5 Timing Charts of The DIPiPM Protective Functions

[A] Short-Circuit Protection (N-side only with the external shunt resistor and RC filter)

a1. Normal operation: IGBT ON and outputs current.
a2. Short circuit current detection (SC trigger)
   (It is recommended to set RC time constant 1.5~2.0μs so that IGBT shut down within 2.0μs when SC.)
a3. All N-side IGBT’s gates are hard interrupted.
a4. All N-side IGBTs turn OFF.
a5. F0 outputs for $t_{fo}=\text{minimum} 20\mu s$.
a6. Input = “L”: IGBT OFF
a7. Fo finishes output, but IGBTs don’t turn on until inputting next ON signal (L→H).
   (IGBT of each phase can return to normal state by inputting ON signal to each phase.)
a8. Normal operation: IGBT ON and outputs current.

B] Under-Voltage Protection (N-side, UV₀)

b1. Control supply voltage $V_D$ exceeds under voltage reset level (UV₀₃), but IGBT turns ON by next ON signal (L→H).
   (IGBT of each phase can return to normal state by inputting ON signal to each phase.)
b2. Normal operation: IGBT ON and outputs current.
b3. $V_D$ level drops to under voltage trip level. (UV₀₄).
b4. All N-side IGBTs turn OFF in spite of control input condition.
b5. Fo outputs for $t_{fo}=\text{minimum} 20\mu s$, but output is extended during $V_D$ keeps below UV₀₃.
b6. $V_D$ level reaches UV₀₃.
b7. Normal operation: IGBT ON and outputs current.

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MITSUBISHI ELECTRIC CORPORATION
[C] Under-Voltage Protection (P-side, UV_{DB})
   c1. Control supply voltage $V_{DB}$ rises. After the voltage reaches under voltage reset level $UV_{DBr}$, IGBT turns on by next ON signal (L $\rightarrow$ H).
   c2. Normal operation: IGBT ON and outputs current.
   c3. $V_{DB}$ level drops to under voltage trip level ($UV_{DBt}$).
   c4. IGBT of the correspond phase only turns OFF in spite of control input signal level, but there is no $F_o$ signal output.
   c5. $V_{DB}$ level reaches $UV_{DBr}$.

[D] Over Temperature Protection (N-side, Detecting LVIC temperature)
   d1. Normal operation: IGBT ON and outputs current.
   d2. LVIC temperature exceeds over temperature trip level ($OT_t$).
   d3. All N-side IGBTs turn OFF in spite of control input condition.
   d4. $F_o$ outputs for $t_{Fo}$=minimum 20$\mu$s, but output is extended during LVIC temperature keeps over $OT_t$.
   d5. LVIC temperature drops to over temperature reset level.
   d6. Normal operation: IGBT turns on by next ON signal (L $\rightarrow$ H).
   (IGBT of each phase can return to normal state by inputting ON signal to each phase.)
(1) If control GND is connected with power GND by common broad pattern, it may cause malfunction by power GND fluctuation. It is recommended to connect control GND and power GND at only a point N1 (near the terminal of shunt resistor).

(2) It is recommended to insert a Zener diode D1(24V/1W) between each pair of control supply terminals to prevent surge destruction.

(3) To prevent surge destruction, the wiring between the smoothing capacitor and the P, N1 terminals should be as short as possible. Generally a 0.1-0.22μF snubber capacitor C3 between the P-N1 terminals is recommended.

(4) R1, C4 of RC filter for preventing protection circuit malfunction is recommended to select tight tolerance, temp-compensated type. The time constant R1C4 should be set so that SC current is shut down within 2μs. (1.5μs~2μs is general value.) SC interrupting time might vary with the wiring pattern, so the enough evaluation on the real system is necessary.

(5) To prevent malfunction, the wiring of A, B, C should be as short as possible.

(6) The point D at which the wiring to CIN filter is divided should be near the terminal of shunt resistor. NU, NV, NW terminals should be connected near NU, NV, NW terminals.

(7) All capacitors should be mounted as close to the terminals as possible. (C1: good temperature, frequency characteristic electrolytic type and C2:0.22μF, good temperature, frequency and DC bias characteristic ceramic type are recommended.)

(8) Input drive is High-active type. There is a minimum 3.3kΩ pull-down resistor in the input circuit of IC. To prevent malfunction, the wiring of each input should be as short as possible. When using RC coupling circuit, make sure the input signal level meet the turn-on and turn-off threshold voltage.

(9) Fo output is open drain type. It should be pulled up to MCU or control power supply (e.g. 5V,15V) by a resistor that makes Ifo up to 1mA. (Ifo is estimated roughly by the formula of control power supply voltage divided by pull-up resistance. In the case of pulled up to 5V, 10kΩ (5kΩ or more) is recommended.)

(10) Thanks to built-in HVIC, direct coupling to MCU without any opto-coupler or transformer isolation is possible.

(11) Two VAC terminals (9 & 16 pin) are connected inside DIPIPM, please connect either one to the 15V power supply GND outside and leave another one open.

(12) If high frequency noise superimposed to the control supply line, IC malfunction might happen and cause DIPIPM erroneous operation. To avoid such problem, line ripple voltage should meet dV/dt ≤+/-1V/μs, Vripples2Vp-p.

(13) For DIPIPM, it isn't recommended to drive same load by parallel connection with other phase IGBT or other DIPIPM.
When DIPIPM is operated with three shunt resistors, voltage of each shunt resistor cannot be input to CIN terminal directly. In that case, it is necessary to use the external protection circuit as below.

1. It is necessary to set the time constant $R_C$ of external comparator input so that IGBT stops within 2μs when short circuit occurs. SC interrupting time might vary with the wiring pattern, comparator speed and so on.
2. It is recommended for the threshold voltage $V_{ref}$ to set to the same rating of short circuit trip level ($V_{sc(ref)}$: typ. 0.48V).
3. Select the external shunt resistance so that SC trip-level is less than specified value (=1.7 times of rating current).
4. To avoid malfunction, the wiring A, B, C should be as short as possible.
5. The point D at which the wiring to comparator is divided should be close to the terminal of shunt resistor.
6. OR output high level when protection works should be over 0.505V (=maximum $V_{sc(ref)}$ rating).
1) 9 & 16 pins (VNC) are connected inside DIPIPM, please connect either one to the control power supply GND outside and leave another one open.
2) No.17 is VOT for built-in temperature output function type (PSS**S92F6-AG) and NC (No Connection) for built-in OT protection function type (PSS**S92E6-AG).

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# Revision Record

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